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 APPLICANT(S): Currie et al.
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U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>9/10</i>	A1	5,442,205	08/15/1995	Brasen et al.	257	191	08/09/1993
<i>9/10</i>	A2	5,726,087	03/10/1998	Tseng et al.	438	261	06/09/1994
<i>9/10</i>	A3	5,780,922	07/14/1998	Mishra et al.	257	616	11/27/1996
<i>9/10</i>	A4	6,107,653	08/22/2000	Fitzgerald	257	191	06/23/1998
<i>9/10</i>	A5	6,284,615 B1	09/04/2001	Pinto et al.	438	336	06/16/1999
<i>9/10</i>	A6	US2002/0068393 A1	06/06/2002	Fitzgerald et al.	438	172	08/06/2001
<i>9/10</i>	A7	US2003/0230233 A1	12/18/2003	Fitzgerald et al.	117	84	03/19/2003
<i>9/10</i>	A8	US2004/0031979 A1	02/19/2004	Lochtefeld et al.	257	233	06/06/2003

FOREIGN PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
<i>9/10</i>	B1	01/022482 A1	03/29/2001	WO	X	X	X	N	Y
<i>9/10</i>	B2	03/001607 A1	01/03/2003	WO	X	X	X	N	Y

OTHER ART, JOURNAL ARTICLES, ETC.

EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)	
<i>9/10</i>	C1	Currie et al., "Carrier Mobilities and Process Stability of Strained Si n- and p-MOSFETs on SiGe virtual substrates," <i>J. Vac. Sci. Technol. B</i> , 19(6):2268-2279 (2001).
<i>9/10</i>	C2	Kummer et al., "Low Energy Plasma Enhanced Chemical Vapor Deposition," <i>Mat. Sci. & Eng. B</i> 89, 288-295 (2002).
<i>9/10</i>	C3	Leitz et al., "Hole mobility enhancements and alloy scattering-limited mobility in tensile strained Si/SiGe surface channel metal-oxide-semiconductor field-effect transistors," <i>Journal of Applied Physics</i> , 92(7):3745-3751 (2002).
<i>9/10</i>	C4	Lucovsky et al., "Low-temperature plasma-assisted oxidation of Si: a new approach for creation of device-quality Si-SiO ₂ interfaces with deposited dielectrics for applications in Si MOSFET technologies," <i>Journal of Non-Crystalline Solids</i> , 179 354-366 (1994).
<i>9/10</i>	C5	Pal et al., "Gd ₂ O ₃ , Ga ₂ O ₃ (Gd ₂ O ₃), Y ₂ O ₃ , and Ga ₂ O ₃ , as high-k gate dielectrics on SiGe: A comparative study," <i>Journal of Applied Physics</i> , 90(8):4103-4107 (2001).
<i>9/10</i>	C6	Sugii et al., "Role of Si _{1-x} Ge _x buffer layer on mobility enhancement in a strained-Si n-channel metal-oxide-semiconductor field-effect transistor," <i>Applied Physics Letters</i> , 75(19):2948-2950 (1999).
<i>9/10</i>	C7	Invitation to Pay Additional Fees for International Application No. PCT/US 03/34576 mailed on December 17, 2004, 7 pages.

EXAMINER <i>William M. Bravets</i>	DATE CONSIDERED <i>28 APR 05</i>
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